IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Kazunari KURITA et al.

Art Unit: not yet assigned

Application No.: 10/576,321

Examiner: not yet assigned

Filed: 04/19/2006

Attorney Dkt. No.: 12054-0059

For: PROCESS FOR PRODUCING HIGH-RESISTANCE SILICON WAFERS AND

PROCESS FOR PRODUCING EPITAXIAL WAFERS AND SOI WAFERS (AS

AMENDED)

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

As permitted by Rule 1.98(a), copies of the U.S. references are not included herewith.

Applicants respectfully submit that this disclosure is being filed in accordance with 37 C.F.R. 1.97(b), therefore, no fee is required.

Respectfully submitted,

CLARK & BRODY

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Docket No.: 12054-0059

Date: July 24, 2006

FORM PTO-1449

applicant.

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

SERIAL NO.

12054-0059

10/576,321

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

Kazunari KURITA et al.

FILING DATE

APPLICANT

GROUP ART UNIT

04/19/2006

Not yet assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
	1.	6,544,656	04/08/2003	ABE et al.			
	2.	2002/0179003	12/05/2002	IIDA et al.			

FOREIGN PATENT DOCUMENTS

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	DOCUMENT				SUB-	TRA	NSLA	TION
	NO.	DATE	COUNTRY	CLASS	CLASS	YES	NO	PART.
3.	WO00/55397	09/21/2000	PCT					X
4.	2000-100631	04/07/2000	JAPAN					х
5.	1087041A1	03/28/2001	EUROPE			х		
6.	2000-344598	12/12/2000	JAPAN					х
7.	WO01/79593	10/25/2001	PCT		•			х
8.	1229155	08/07/2002	EUROPE			х		
9.	2003-286094	10/07/2003	JAPAN					х
10.	WO03/092065	11/06/2003	РСТ					х
11.	WO2004/008521	01/22/2004	PCT					х

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

14. A.	. Sueoka et al., "Effect of Oxide Precipitate Sizes on the Mechanical Strength of Czochralsk ilicon Wafers", Jpn. J. Appl. Phys., Vol. 36 (1997), pgs. 7095-7099 . Bean et al., "The Effect of Carbon on Thermal Donor Formation in Heat Treated Pulled
	. Bean et al., "The Effect of Carbon on Thermal Donor Formation in Heat Treated Pulled
	ilicon Crystals", J. Phys. Chem. Solids, Vol. 33 (1972), pgs. 255-268
EXAMINER	DATE CONSIDERED